

	Hits	Search Text	DBs
2	1	((vary\$3 or reduc\$4 or decrease or chang\$4 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist) same (substrate or wafer) same (poison\$3 or contaminat\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3)) and ((substrate or wafer) same DARC)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	97	((vary\$3 or reduc\$4 or decrease or chang\$4 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist) same (substrate or wafer) same (poison\$3 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
4	15	((vary\$3 or reduc\$4 or decrease or chang\$4 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist) same (substrate or wafer) same (poison\$3 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3)) and ((photoresist or resist) same (acid\$2 near2 generat\$4) or (photoacid near3 generator) or (acid near3 liberat\$3) or (chemical\$2 near3 (amplification or amplify\$3 or amplified)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	5	((reduc\$4 or decreas\$3 or prevent\$4) same (photoresist or resist) same (substrate or wafer) same (poison\$3 or decomposition) same plasma same (treat\$4 or react\$4)) and ((photoresist or resist) same (acid\$2 near2 generat\$4) or (photoacid near3 generator) or (acid near3 liberat\$3) or (chemical\$2 near3 (amplification or amplify\$3 or amplified))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
6	45	((reduc\$4 or decreas\$3 or prevent\$4) same (photoresist or resist) same (substrate or wafer) same (poison\$3 or decomposition) same plasma same (treat\$4 or react\$4))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
7	51	((reduc\$4 or decreas\$3 or prevent\$4) same (photoresist or resist) same (substrate or wafer) same (poison\$3 or decomposition)) and (plasma same (treat\$4 or react\$4 or ion\$3) same (He or helium or Hydrogen or "H.sub.2"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
8	12	((reduc\$4 or decreas\$3 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist) same (substrate or wafer) same (poison\$3 or contamina\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3)) and ((substrate or wafer or workpice) same (DARC or ((dielectric or inorganic or silicon or Si) near4 (ARC or anti\$3reflect\$3))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
9	26	((reduc\$4 or decreas\$3 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist) same (poison\$3 or contamina\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3)) and ((substrate or wafer or workpice) same (DARC or ((dielectric or inorganic or silicon or Si) near4 (ARC or anti\$3reflect\$3))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
10	27	((reduc\$4 or decreas\$3 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist) same (poison\$3 or contamina\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3)) and ((substrate or wafer or workpice) same (DARC or ((dielectric or inorganic or silicon or Si or SiON or silicon\$3nitride or Si\$2N\$2) near4 (ARC or anti\$3reflect\$3))))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	7	430/322.ccls. and ((vary\$3 or reduc\$4 or decrease or chang\$4 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist) same (substrate or wafer) same (poison\$3 or contamina\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
12	10	430/322.ccls. and ((vary\$3 or reduc\$4 or decrease or chang\$4 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist or BARC or ARC) same (poison\$3 or contamina\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
13	13	427/569.ccls. and ((vary\$3 or reduc\$4 or decrease or chang\$4 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist or BARC or ARC) same (poison\$3 or contamina\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
14	3	427/535.ccls. and ((vary\$3 or reduc\$4 or decrease or chang\$4 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist or BARC or ARC) same (poison\$3 or contamina\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	4	427/578.ccls. and ((vary\$3 or reduc\$4 or decrease or chang\$4 or remov\$4 or eliminat\$4 or prevent\$4) same (photoresist or resist or BARC or ARC) same (poison\$3 or contamina\$4 or decomposition) same plasma same (treat\$4 or react\$4 or ion\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB